

**High Power Linear Amplifier
2.3 – 2.8 GHz**

**MAAPSS0103
V3**

Features

- Ideal for WiMax, MESH Network, and Linear Applications
- P1dB: +32 dBm Typical
- Small Signal Gain: 34 dB Typical
- EVM: 2.5% at 26 dBm Linear (OFDM) P_{OUT}
- Integrated Detector
- Lead-Free 4 mm 16 lead PQFN Package
- 100% Matte Tin Plating over Copper
- Halogen-Free “Green” Mold Compound
- RoHS* Compliant and 260°C Reflow Compatible

Description

M/A-COM’s MAAPSS0103 RF power amplifier is a three stage GaAs MMIC which exhibits high gain and linearity performance in a lead-free 4 mm 16-lead PQFN surface mount plastic package. This product is designed for the 2.5 GHz IEEE 802.16 / WiMax band. The MAAPSS0103 also features an integrated power detector.

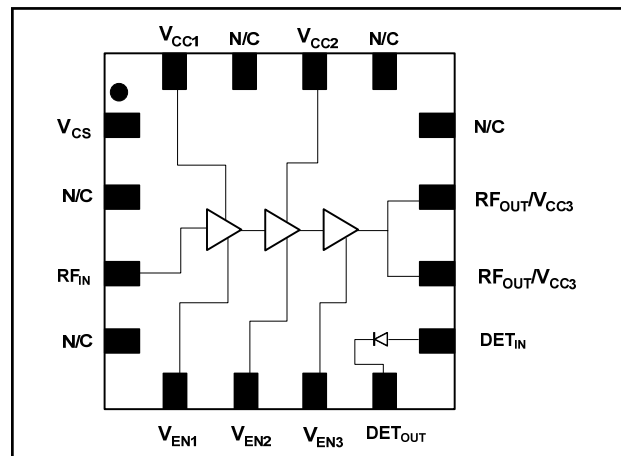
The MAAPSS0103 is fabricated using a high reliability GaAs HBT process to realize low current and high power functionality. The process features full passivation for increased performance and reliability.

Ordering Information ¹

| Part Number | Package |
|-------------------|--|
| MAAPSS0103TR-1000 | 1000 piece reel |
| MAAPSS0103TR-3000 | 3000 piece reel |
| MAAPSS0103SMB | Sample Test Board (Includes 5 Samples) |

1. Reference Application Note M513 for reel size information.

Block Diagram



Pin Configuration

| Pin No. | Pin Name | Description |
|---------|-------------------------------------|-----------------------------|
| 1 | V _{CS} | Bias Supply Voltage |
| 2 | N/C | No Connect |
| 3 | RF _{IN} | RF Input |
| 4 | N/C | No Connect |
| 5 | V _{EN1} | Power Enable |
| 6 | V _{EN2} | Power Enable |
| 7 | V _{EN3} | Power Enable |
| 8 | DET _{OUT} | Detector Output |
| 9 | DET _{IN} | Detector Input |
| 10 | RF _{OUT} /V _{CC3} | RF Output, 3rd Stage Supply |
| 11 | RF _{OUT} /V _{CC3} | RF Output, 3rd Stage Supply |
| 12 | N/C | No Connect |
| 13 | N/C | No Connect |
| 14 | V _{CC2} | 2nd Stage Supply |
| 15 | N/C | No Connect |
| 16 | V _{CC1} | 1st Stage Supply |
| 17 | Paddle ² | RF & DC Ground |

2. The exposed pad centered on the package bottom must be connected to RF and DC ground.

* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

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Electrical Specifications: $T_A = +25\text{ }^\circ\text{C}$, $V_{CC} = 5.0\text{ V}$, $Z_0 = 50\text{ }\Omega$

| Parameter | Test Conditions | Units | Min. | Typ. | Max. |
|--|---|--------------------|--------|------------|----------|
| Gain | 2.5 GHz | dB | 31 | 34 | — |
| Gain Flatness | 2.3 - 2.8 GHz | dB | — | ± 1 | — |
| Input Return Loss | 2.3 - 2.8 GHz | dB | — | 10 | — |
| Output Return Loss | 2.3 - 2.8 GHz | dB | — | 10 | — |
| Output P1dB | 2.5 GHz | dBm | — | 32 | — |
| EVM ³ | 2.5 GHz, $P_{OUT} = 26\text{ dBm}$ OFDM, QAM-64, 54 Mbps | % | — | 2.5 | — |
| Enable Voltage | V_{EN} | V | — | 2.8 | — |
| Device / Supply Voltage | 2.3 - 2.8 GHz | V | — | 5 | — |
| Quiescent Current Operating Current | 2.5 GHz, No RF 2.5 GHz, $P_{OUT} = 26\text{ dBm}$ | mA mA | — — | 250 600 | — 700 |
| PAE | 2.5 GHz, $P_{OUT} = 26\text{ dBm}$ | % | — | 14 | — |
| Detector Output Range | 2.5 GHz, $P_{OUT} = 14 - 28\text{ dBm}$, OFDM | V | — | 0.5 - 2.0 | — |
| Thermal Resistance | @ $85\text{ }^\circ\text{C}$ package paddle temperature | $^\circ\text{C/W}$ | — | 25 | — |

3. Includes system EVM of 0.8%.

Absolute Maximum Ratings^{4,5}

| Parameter | Absolute Maximum |
|---------------------------|---|
| Input Power | + 5 dBm |
| Operating Supply Voltage | +6.0 Volts |
| Operating Control Voltage | +3.6 Volts |
| Operating Temperature | -40 $^\circ\text{C}$ to +85 $^\circ\text{C}$ |
| Channel Temperature | +150 $^\circ\text{C}$ |
| Storage Temperature | -40 $^\circ\text{C}$ to +150 $^\circ\text{C}$ |

4. Exceeding any one or combination of these limits may cause permanent damage to this device.

5. M/A-COM does not recommend sustained operation near these survivability limits.

Handling Procedures

Please observe the following precautions to avoid damage:

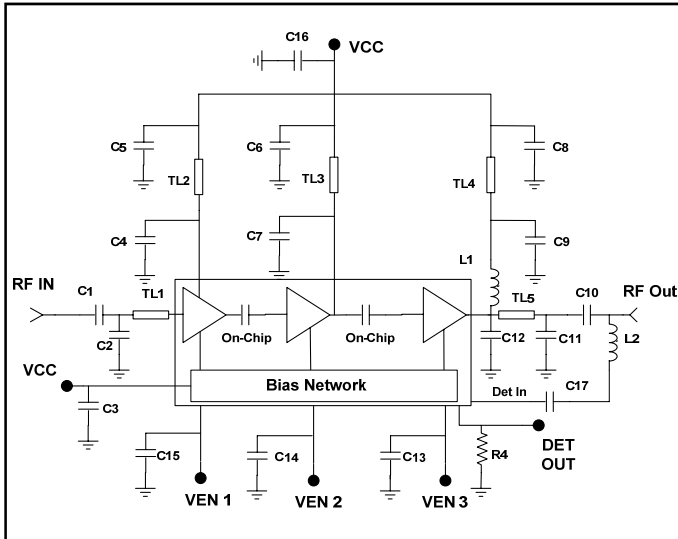
Static Sensitivity

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

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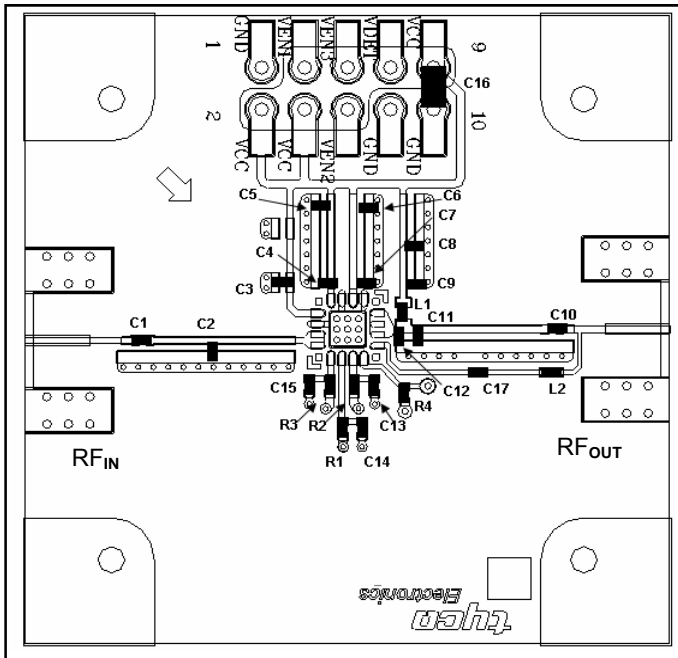
Application Schematic



External Parts List

| Component | Value | Case Size | Manufacturer |
|-----------------------|----------------------------|-----------|--------------|
| C1, C5, C6, C10, C17 | 1000 pF | 0402 | Murata |
| C2 | 1.8 pF | 0402 | Murata |
| C3, C8, C13, C14, C15 | 0.1 μ F | 0402 | Murata |
| C4, C7, C9 | 8 pF | 0402 | Murata |
| C11 | 2 pF | 0402 | Murata |
| C12 | 2.2 pF | 0402 | Murata |
| C16 | 3.3 μ F | 1206 | Kemet |
| L1 | 3.6 nH | 0402 | Coilcraft |
| L2 | 15 nH | 0402 | Coilcraft |
| R1,R2,R3 | 0 Ω | — | — |
| R4 | 100 k Ω | — | — |
| TL1 | 5.5 mm (L), 0.37 mm (W) | — | — |
| TL2, TL3 | 4 mm (L), 0.37 mm (W) | — | — |
| TL4 | 1.7 mm (L), 0.37 mm (W) | — | — |
| TL5 | 0.3 mm (L), 0.37 mm (W) | — | — |

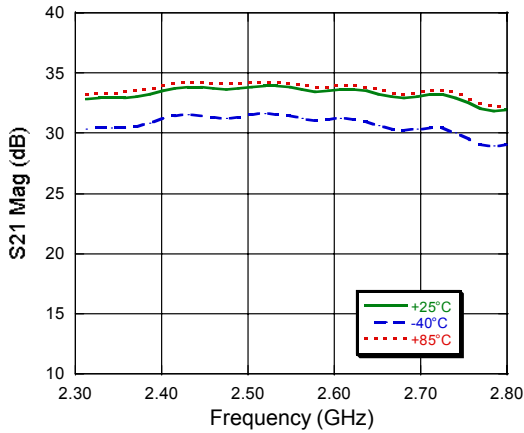
Sample Board ⁶



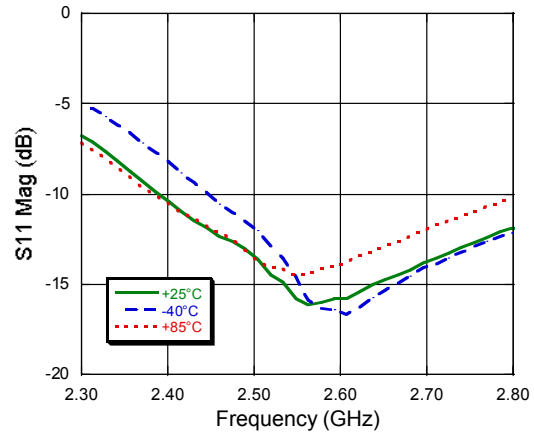
6. PCB Material FR4 - 50 Ω Line = 0.37 mm (W)

Typical Performance Curves: over temp

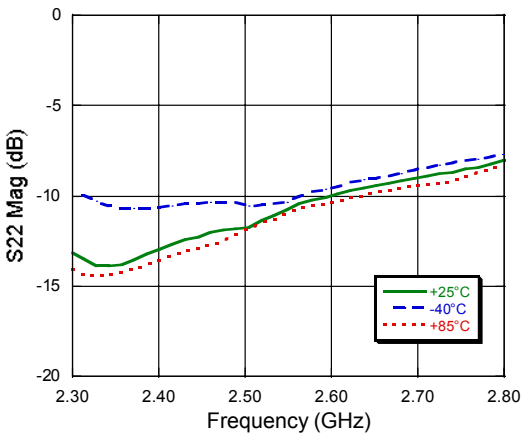
Gain



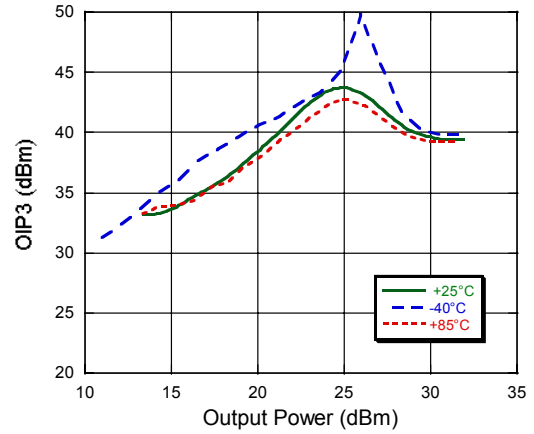
S11



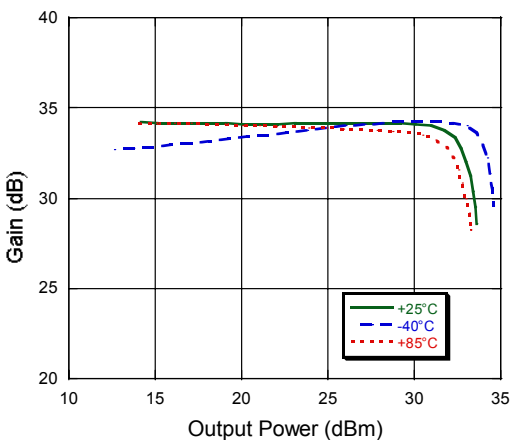
S22



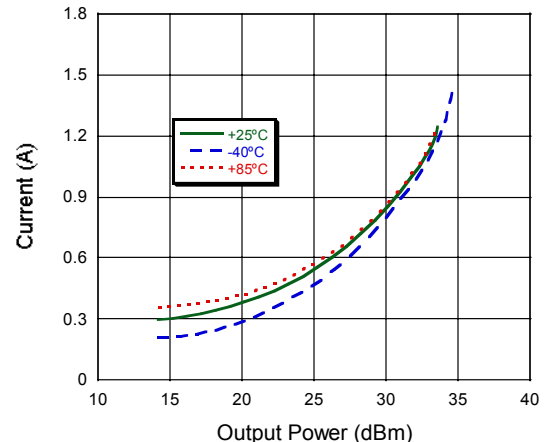
OIP3



P1dB



Current

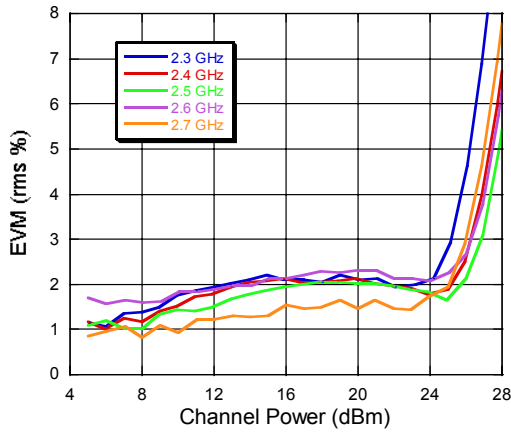


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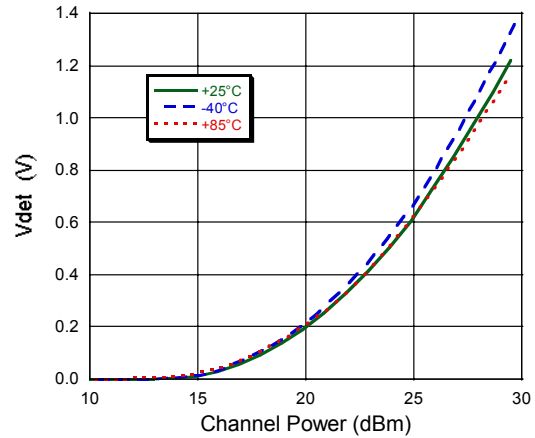
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Typical Performance Curves: @ +25°C

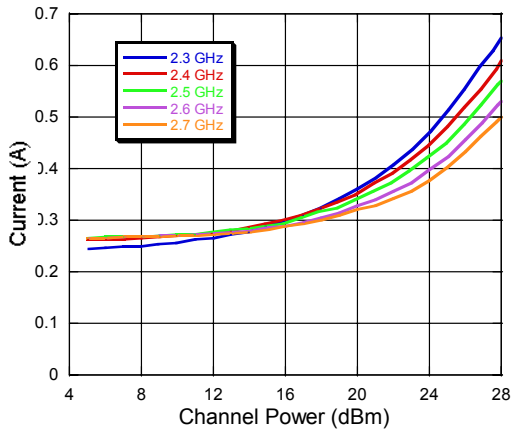
EVM vs. Channel Power



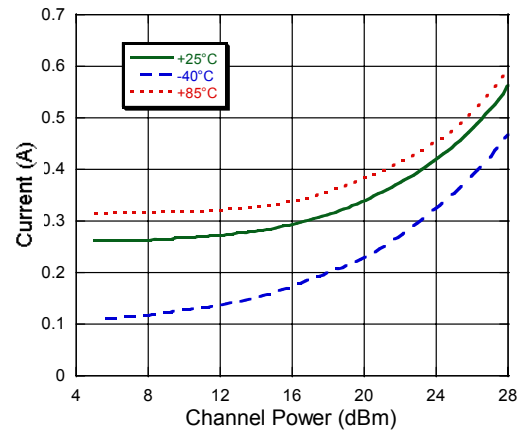
V_{DET} vs. Channel Power Over Temp @ 2.5 GHz



Current vs. Channel Power



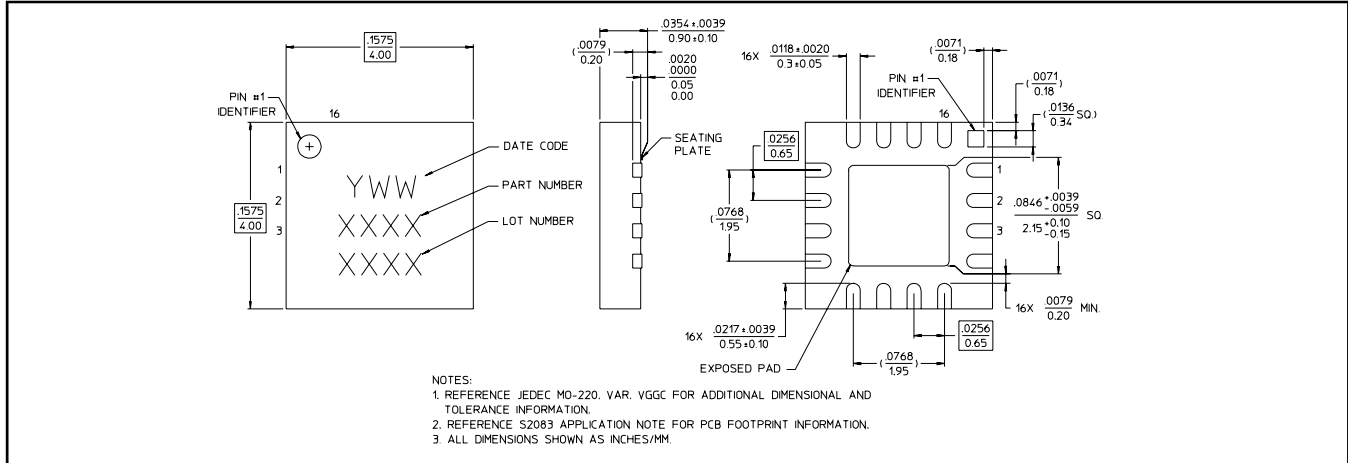
Current vs. Channel Power Over Temp @ 2.5 GHz



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Lead-Free 4 mm 16-Lead PQFN†



† Reference Application Note M538 for lead-free solder reflow recommendations.
Meets JEDEC moisture sensitivity level 1 requirements.